# Bias Resistor Transistor

NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

- **Applications**
  Inverter, Interface, Driver

- **Features**
  1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
  2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
  3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LDTD123YLT1G
S-LDTD123YLT1G

SOT–23

3 COLLECTOR

1 BASE

2 EMITTER

●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V_{CC}	50	V
Input voltage	V_{IN}	−5 to +12	V
Output current	I_C	500	mA
Power dissipation	Pd	200	mW
Junction temperature	Tj	150	C
Storage temperature	Tstg	−55 to +150	C
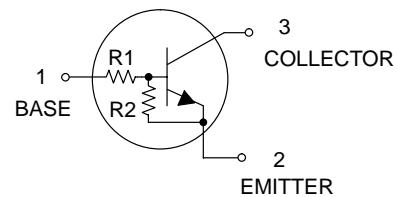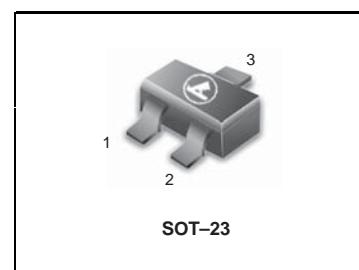
DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTD123YLT1G S-LDTD123YLT1G	F62	2.2	10	3000/Tape & Reel
LDTD123YLT3G S-LDTD123YLT3G	F62	2.2	10	10000/Tape & Reel

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	–	–	0.3	V	V_{CC}=5V, I_O=100μA
	$V_{I(on)}$	2	–	–		V_O=0.3V, I_O=20mA
Output voltage	$V_{O(on)}$	–	0.1	0.3	V	I_O/I_I=50mA/2.5mA
Input current	I_I	–	–	3.6	mA	V_I=5V
Output current	$I_{O(off)}$	–	–	0.5	μA	V_{CC}=50V, V_I=0V
DC current gain	G_I	56	–	–	–	V_O=5V, I_O=50mA
Input resistance	R_1	1.54	2.2	2.86	kΩ	–
Resistance ratio	R_2/R_1	3.6	4.5	5.5	–	–
Transition frequency	f_T	–	200	–	MHz	V_{CE}=10V, I_E= −50mA, f=100MHz ＊

＊Transition frequency of the device

LDTD123YLT1G;S-LDTD123YLT1G

●**Electrical characteristic curves**
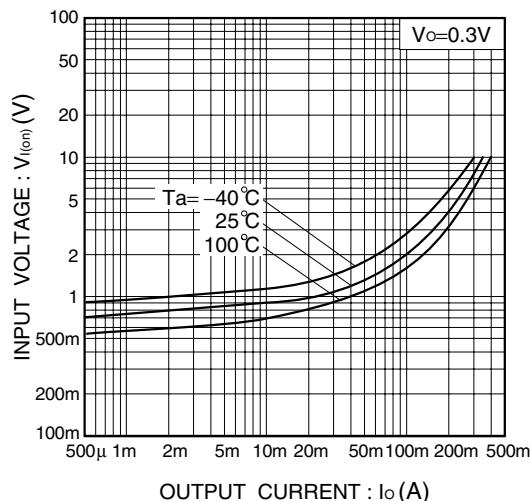
Fig.1   Input voltage vs. output current
(ON characteristics)
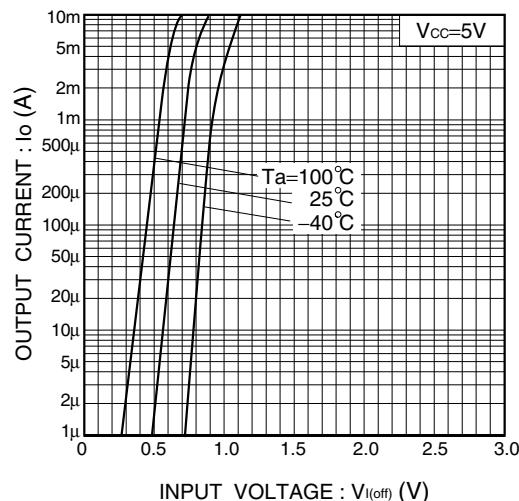
Fig.2   Output current vs. input voltage
(OFF characteristics)
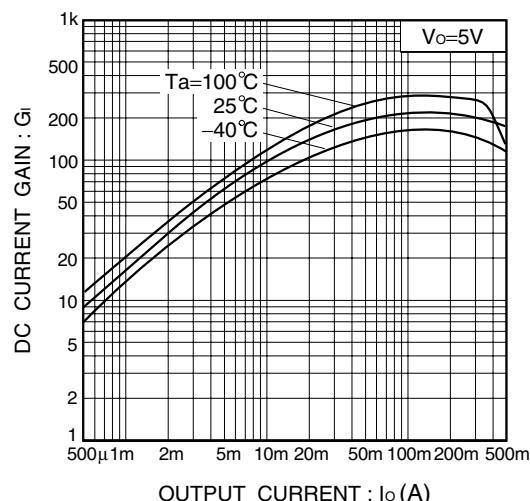

Fig.3   DC current gain vs. output current
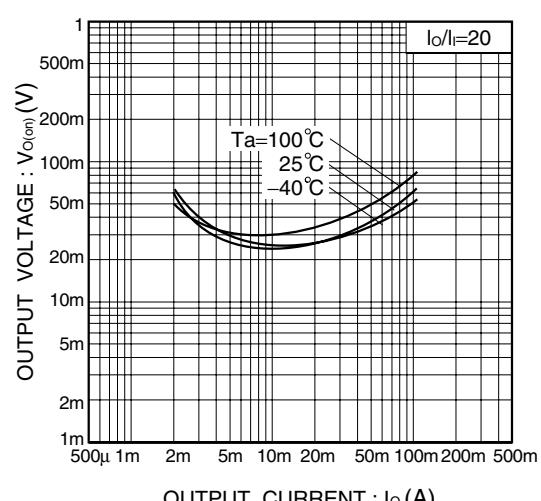
Fig.4   Output voltage vs. output current

LDTD123YLT1G；S-LDTD123YLT1G

SOT−23

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.
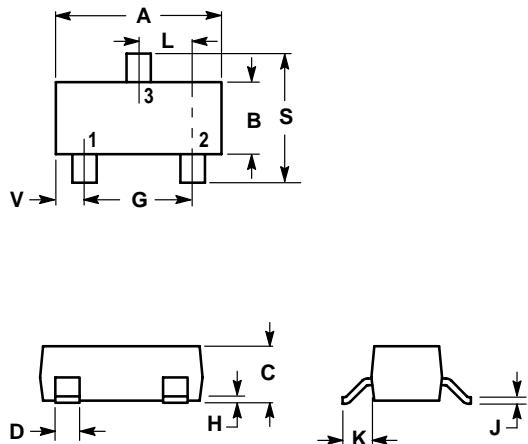
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

$\frac{0.037}{0.95}$

$\frac{0.037}{0.95}$

$\frac{0.079}{2.0}$

$\frac{0.035}{0.9}$

$\frac{0.031}{0.8}$

$\left(\frac{\text{inches}}{\text{mm}}\right)$
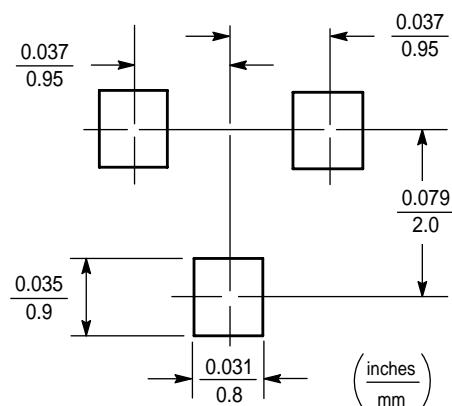
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